

FROM ARMSTRONG, WESTERMAN

(MON) 2.25'02 13:43/ST.13:42/NO.4864272874 P 1

Law Offices

ARMSTRONG, WESTERMAN & HATTORI, LLP
Suite 1000, 1725 K Street
Washington, D.C. 20006

(202) 659-2930

Faxsimile (202) 887-0357 or (202) 331-7519

FACSIMILE TRANSMISSION COVER SHEET

DATE: February 25, 2002

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TO: Examiner Jack Chen
Group Art Unit: 2813

FEB 25 2002

RE: Preliminary Amendment
U.S. Patent Appln. S.N. 09/321,605
By: SASHIDA et al.
Our Reference: P3329-698-A990535

TECHNOLOGY CENTER 2800

FROM: Thomas E. Brown

FAC. TEL. NO.: 703-746-3890 *or 703-308-7722 or 7724*

NUMBER OF PAGES (INCLUDING THIS COVER SHEET): 12

Dear Examiner Chen:

As requested by you earlier today on the telephone, attached is a copy of the Preliminary Amendment filed February 15, 2002.

PLEASE ACKNOWLEDGE SAFE AND CLEAR RECEIPT OF ALL PAGES BEING SENT

TEB/kas *70*

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

SASHIDA et al.

Serial Number: 09/321,605

Group Art Unit: 2813

Filed: May 28, 1999

Examiner: J. Chen

For: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE HAVING CAPACITOR

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

February 15, 2002

Sir:

Prior to examination on the merits, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 21 as follows:

- Sub 41
1. (Three Amended) A method of manufacturing a semiconductor device comprising the steps of:
forming a couple of impurity diffusion layers in a semiconductor substrate;
forming a first insulating film covering the semiconductor substrate;
forming a lower electrode of a capacitor on the first insulating film;
forming an oxide dielectric film of the capacitor on the lower electrode;